L Number	Hits	Search Text	DB	Time stamp
-	628447	DRAM\$1 or (dynamic adj random adj access adj memor\$4) or	USPAT;	2004/03/15 11:54
		capacitor\$1	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM TDB	
_	12833	vertical\$4 near3 (MOS or transistor\$1 or MOSFET\$1)	USPAT;	2004/03/15 15:50
	12033	(2.200 0. 2.2	US-PGPUB;	
			ЕРО; ЛРО;	
	i		DERWENT;	
			IBM_TDB	
	3878	(DRAM\$1 or (dynamic adj random adj access adj memor\$4) or	USPAT;	2004/03/15 11:55
-	5676	capacitor\$1) and (vertical\$4 near3 (MOS or transistor\$1 or	US-PGPUB;	200 (100) 10 11100
		MOSFET\$1))	ЕРО; ЛРО;	
		[ NOSPET#1))	DERWENT;	
			IBM TDB	
	24706	(hum, or humod) near? (layor\$1 or film\$1)	USPAT;	2004/03/15 11:56
	34706	(bury or buried) near3 (layer\$1 or film\$1)	US-PGPUB;	2004/03/13 11.30
			EPO; JPO;	
			DERWENT;	
	552	(CDD 43 (01	IBM_TDB	2004/02/15 12:40
-	753		USPAT;	2004/03/15 12:40
		capacitor\$1) and (vertical\$4 near3 (MOS or transistor\$1 or	US-PGPUB;	
		MOSFET\$1))) and ((bury or buried) near3 (layer\$1 or film\$1))	ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
-	0	20040014329.URPN.	USPAT	2004/03/15 12:00
-	268974	source\$1 and drain\$1	USPAT;	2004/03/15 12:40
			US-PGPUB;	
			ЕРО, ЈРО,	
			DERWENT;	
			IBM_TDB	
-	16200	(remov\$4 or etch\$4) same drain\$1 same (substrate or wafer) same	USPAT;	2004/03/15 12:42
		(hole\$1 or trench\$2 or via\$1 or open\$5 or groov\$3)	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
-	756023	(top or upper or second) near4 (plate\$1 or electrode\$1)	USPAT;	2004/03/15 12:43
			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
-	121	(((DRAM\$1 or (dynamic adj random adj access adj memor\$4) or	USPAT;	2004/03/15 12:44
		capacitor\$1) and (vertical\$4 near3 (MOS or transistor\$1 or	US-PGPUB;	
		MOSFET\$1))) and ((bury or buried) near3 (layer\$1 or film\$1))) and	ЕРО; ЈРО;	
		(source\$1 and drain\$1) and ((remov\$4 or etch\$4) same drain\$1 same	DERWENT;	
		(substrate or wafer) same (hole\$1 or trench\$2 or via\$1 or open\$5 or	IBM_TDB	
		groov\$3)) and ((top or upper or second) near4 (plate\$1 or electrode\$1))		
l -	47376	storag\$4 near4 (plate\$1 or electrode\$1)	USPAT;	2004/03/15 12:45
[			US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	

	<u> </u>	(DD 1) (D) 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	LICDATE	2004/02/15 12 40
-	53	((DRAM\$1 or (dynamic adj random adj access adj memor\$4) or	USPAT;	2004/03/15 12:49
		capacitor\$1) and (vertical\$4 near3 (MOS or transistor\$1 or	US-PGPUB;	
		MOSFET\$1))) and (source\$1 and drain\$1) and ((remov\$4 or etch\$4)	ЕРО; ЛРО;	
		same drain\$1 same (substrate or wafer) same (hole\$1 or trench\$2 or	DERWENT;	
		via\$1 or open\$5 or groov\$3)) and ((top or upper or second) near4	IBM_TDB	
		(plate\$1 or electrode\$1)) and ((((DRAM\$1 or (dynamic adj random adj		
		access adj memor\$4) or capacitor\$1) and (vertical\$4 near3 (MOS or		
		transistor\$1 or MOSFET\$1))) and ((bury or buried) near3 (layer\$1 or		
		film\$1))) and (source\$1 and drain\$1) and ((remov\$4 or etch\$4) same		
		drain\$1 same (substrate or wafer) same (hole\$1 or trench\$2 or via\$1 or		
		open\$5 or groov\$3)) and ((top or upper or second) near4 (plate\$1 or		
		electrode\$1))) and (storag\$4 near4 (plate\$1 or electrode\$1))		
-	758663	(lower or bottom or first) near4 (electrode\$1 or plate\$1)	USPAT;	2004/03/15 15:42
			US-PGPUB;	
			ЕРО, ЈРО,	
			DERWENT;	
	•		IBM TDB	
_	968	((438/243) or (438/244) or (438/245) or (438/246) or (438/247) or	USPAT;	2004/03/15 15:45
_		(438/248) or (438/249)). CCLS.	US-PGPUB	200,100,10
_	741	((438/386) or (438/387) or (438/388) or (438/389) or (438/390) or	USPAT;	2004/03/15 15:46
_	/ - 1	(438/391) or (438/392)).CCLS.	US-PGPUB	200 1/03/13 13.40
-	1293	(((438/243) or (438/244) or (438/245) or (438/246) or (438/247) or	USPAT;	2004/03/15 15:47
	12,3	((438/248) or (438/249)). CCLS.) or (((438/386) or (438/387) or	US-PGPUB	200 1/03/13 13:17
		(438/388) or (438/389) or (438/390) or (438/391) or (438/392)).CCLS.)	OB-1 GI OD	
	1892	(438/136) or (438/137) or (438/138) or (438/206) or (438/241) or	USPAT;	2004/03/15 15:50
_	1072	(438/242) or (438/268) or (438/270) or (438/271)).CCLS.	US-PGPUB	2004/03/13 13.30
	46651	vertical\$4 near3 (MOS or transistor\$1 or MOSFET\$1 or channel\$3)	USPAT;	2004/03/15 15:50
-	40031	Vertical 94 lical 3 (1910) of transistors of the two Str E 1 5 for channel 65)	US-PGPUB;	2004/03/13 13.30
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
	124	(vertical\$4 near3 (MOS or transistor\$1 or MOSFET\$1 or channel\$3))	USPAT;	2004/03/15 16:08
-	124			2004/03/13 10.08
		and (DRAM\$1 or (dynamic adj random adj access adj memor\$4) or	US-PGPUB;	
		capacitor\$1) and ((bury or buried) near3 (layer\$1 or film\$1)) and	ЕРО; ЛРО;	
		(source\$1 and drain\$1) and ((remov\$4 or etch\$4) same drain\$1 same	DERWENT;	
	ŀ	(substrate or wafer) same (hole\$1 or trench\$2 or via\$1 or open\$5 or	IBM_TDB	
		groov\$3)) and ((top or upper or second) near4 (plate\$1 or electrode\$1))		
		and ((storag\$4 near4 (plate\$1 or electrode\$1)) or ((lower or bottom or		
		first) near4 (electrode\$1 or plate\$1)))		
-	131	(((438/136) or (438/137) or (438/138) or (438/206) or (438/241) or	USPAT;	2004/03/15 16:09
		(438/242) or (438/268) or (438/270) or (438/271)).CCLS.) and	US-PGPUB;	
		(DRAM\$1 or (dynamic adj random adj access adj memor\$4) or	ЕРО; ЈРО;	
		capacitor\$1) and (vertical\$4 near3 (MOS or transistor\$1 or MOSFET\$1	DERWENT;	
		or channel\$3)) and ((top or upper or second) near4 (plate\$1 or	IBM_TDB	
		electrode\$1)) and ((storag\$4 near4 (plate\$1 or electrode\$1)) or ((lower		
	i	or bottom or first) near4 (electrode\$1 or plate\$1)))		
				1 0004/00/17 16 00
-	129	((((438/243) or (438/244) or (438/245) or (438/246) or (438/247) or	USPAT;	2004/03/15 16:09
-	129	(438/248) or (438/249)).CCLS.) or (((438/386) or (438/387) or	US-PGPUB;	2004/03/15 16:09
-	129			2004/03/15 16:09
-	129	(438/248) or (438/249)).CCLS.) or (((438/386) or (438/387) or (438/388) or (438/389) or (438/390) or (438/391) or (438/392)).CCLS.)) and (DRAM\$1 or (dynamic adj random adj access adj memor\$4) or	US-PGPUB;	2004/03/15 16:09
-	129	(438/248) or (438/249)).CCLS.) or (((438/386) or (438/387) or (438/388) or (438/389) or (438/390) or (438/391) or (438/392)).CCLS.))	US-PGPUB; EPO, JPO;	2004/03/15 16:09
-	129	(438/248) or (438/249)).CCLS.) or (((438/386) or (438/387) or (438/388) or (438/389) or (438/390) or (438/391) or (438/392)).CCLS.)) and (DRAM\$1 or (dynamic adj random adj access adj memor\$4) or	US-PGPUB; EPO; JPO; DERWENT;	2004/03/15 16:09
-	129	(438/248) or (438/249)).CCLS.) or (((438/386) or (438/387) or (438/388) or (438/389) or (438/390) or (438/391) or (438/392)).CCLS.)) and (DRAM\$1 or (dynamic adj random adj access adj memor\$4) or capacitor\$1) and (vertical\$4 near3 (MOS or transistor\$1 or MOSFET\$1	US-PGPUB; EPO; JPO; DERWENT;	2004/03/15 16:09